

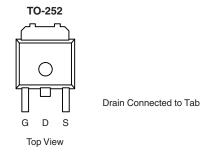
N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
100	0.025 at V <sub>GS</sub> = 10 V	40		
100	0.028 at V <sub>GS</sub> = 4.5 V	38		

#### **FEATURES**

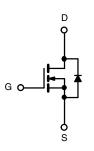
- TrenchFET® Power MOSFET
- 175 °C Maximum Junction Temperature
- 100 % R<sub>q</sub> Tested





Ordering Information: SUD40N10-25

SUD40N10-25-E3 (Lead (Pb)-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	100	_ v		
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Continuous Drain Current /T 175 °C\D	T <sub>C</sub> = 25 °C	L	40			
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C	l ID	23			
Pulsed Drain Current		I <sub>DM</sub>	70	Α		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	40				
Avalanche Current	I <sub>AS</sub>	40	7			
Single Pulse Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	80	mJ		
Maximum Davier Dissination	T <sub>C</sub> = 25 °C	ь	136 <sup>b</sup>	10/		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3 <sup>a</sup>	W		
Operating Junction and Storage Temperature Range	·	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Lucation to Ambiomt	t ≤ 10 s	- R <sub>thJA</sub>	15	18	°C/W		
Junction-to-Ambient <sup>a</sup>	Steady State		40	50			
Junction-to-Case		R <sub>thJC</sub>	0.85	1.1			

#### Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



### N-Channel 100 V (D-S) 175 °C MOSFET

Parameter	Symbol	ol Test Conditions		Typ. <sup>a</sup>	Max.	Unit	
Static					l		
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	$I_{DSS}$	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50		
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	70			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		0.02	0.025		
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 125 °C			0.05	Ω	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 175 °C			0.063		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.022	0.028		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 40 A		70		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			2400			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, F = 1 \text{ MHz}$		290		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			120		1	
Total Gate Charge <sup>c</sup>	$Q_g$			40	60		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$		11		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			9			
Gate Resistance	$R_g$		1		3.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	13		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_{L} = 1.25 \Omega$		40	60	no	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 40 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		15	25	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			80	120		
Source-Drain Diode Ratings and Cha	racteristics -	Γ <sub>C</sub> = 25 °C		_			
Pulsed Current	I <sub>SM</sub>				70	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 40 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 40 A, dl/dt = 100 A/μs		75	120	ns	

#### Notes

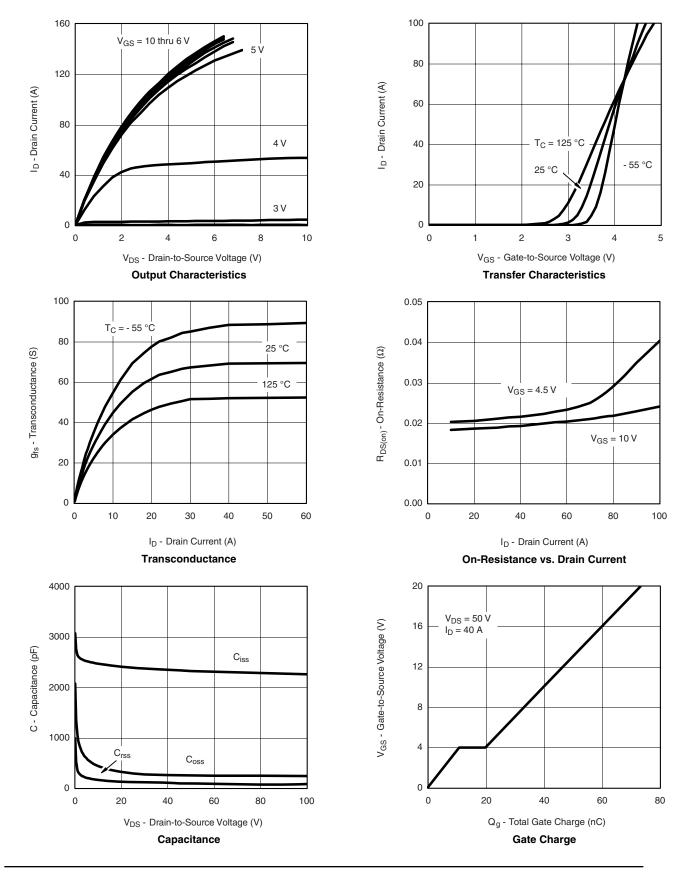
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



N-Channel 100 V (D-S) 175 °C MOSFET

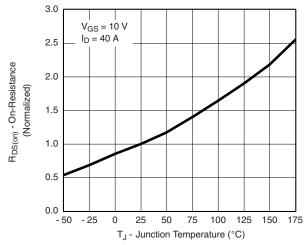
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





N-Channel 100 V (D-S) 175 °C MOSFET

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

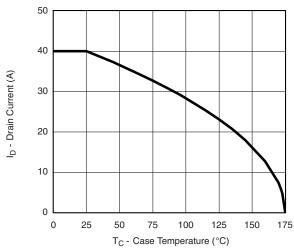


On-Resistance vs. Junction Temperature

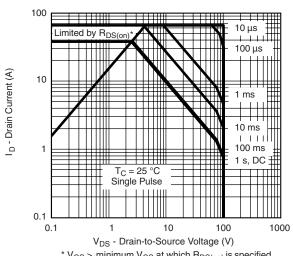
### 

Source-Drain Diode Forward Voltage

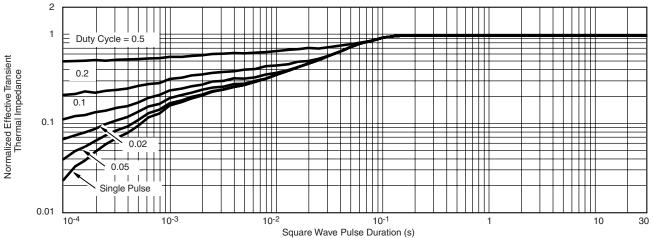
#### THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



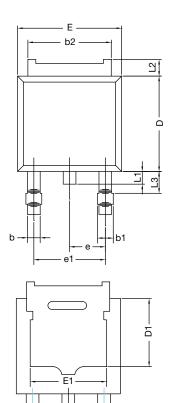
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified **Safe Operating Area** 

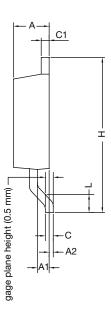


Normalized Thermal Transient Impedance, Junction-to-Case

# N-Channel 100 V (D-S) 175 °C MOSFET

### **TO-252AA CASE OUTLINE**





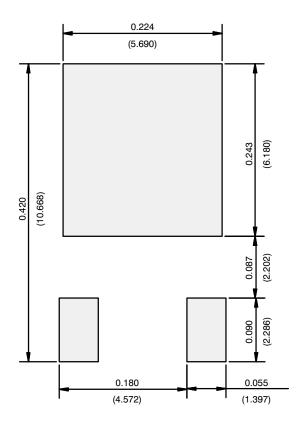
	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090	BSC	
e1	4.57	BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

#### Note

• Dimension L3 is for reference only.

N-Channel 100 V (D-S) 175 °C MOSFET

### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



N-Channel 100 V (D-S) 175 °C MOSFET

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

freestyle Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on it s or their behalf (collectively, "freestyle"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

freestyle makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vi shay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation specia I, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain type s of applications are based on freestyle's knowledge of typical requirements that are often placed on freestyle products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specification s may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify freestyle's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, freestyle products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the freestyle product could result in personal injury or death. Customers using or selling freestyle products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold freestyle and its distributors harmless from and against an y and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vis hay

### **Material Category Policy**

freestyle Intertechnology, Inc. hereby certi fies that all its products that are id entified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some freestyle documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002 /95/EC conform to Directive 2011/65/EU.